



## STP60NE06L-16 Information



For Reference Only

Part Number STP60NE06L-16
Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 60V 60A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









# STP60NE06L-16 Specifications

Manufacturer Part Number         STP60NE06L-16           Manufacturer         STMicroelectronics           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         STripFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         60A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         70nC @ 5V           Input Capacitance (Ciss) (Max) @ Vds         4150pF @ 25V           Vgs (Max)         ±15V           FET Feature         -           Power Dissipation (Max)         150W (Tc)           Rds On (Max) @ Id, Vgs         14 mOhm @ 30A, 10V           Operating Temperature         175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3           Report errors?		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         STripFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         60A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         70nC @ 5V           Input Capacitance (Ciss) (Max) @ Vds         4150pF @ 25V           Vgs (Max)         ±15V           FET Feature         -           Power Dissipation (Max)         150W (Tc)           Rds On (Max) @ Id, Vgs         14 mOhm @ 30A, 10V           Operating Temperature         175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3	Manufacturer Part Number	STP60NE06L-16
Package         TO-220-3           Series         STripFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         60A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         70nC @ 5V           Input Capacitance (Ciss) (Max) @ Vds         4150pF @ 25V           Vgs (Max)         ±15V           FET Feature         -           Power Dissipation (Max)         150W (Tc)           Rds On (Max) @ Id, Vgs         14 mOhm @ 30A, 10V           Operating Temperature         175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-20AB           Package / Case         TO-220-3	Manufacturer	STMicroelectronics
PackageTO-220-3SeriesSTripFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C60A (Tc)Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id2.5 V @ 250μAGate Charge (Qg) (Max) @ Vgs70nC @ 5VInput Capacitance (Ciss) (Max) @ Vds4150pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs14 mOhm @ 30A, 10VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Category	Discrete Semiconductor Products
SeriesSTripFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C60A (Tc)Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs70nC @ 5VInput Capacitance (Ciss) (Max) @ Vds4150pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs14 mOhm @ 30A, 10VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 60A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 70nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 4150pF @ 25V Vgs (Max) ±15V FET Feature - Power Dissipation (Max) 150W (Tc) Rds On (Max) @ Id, Vgs 14 mOhm @ 30A, 10V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package 70-220AB Package / Case	Package	TO-220-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 60A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max)  FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 30A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case  MOSFET (Metal Oxide)  60V  60V  60A (Tc)  60A (Tc)  70nC @ 5V  4150P @ 25V  4150PF @ 25V  4150P ( To)  150W (Tc)  14 mOhm @ 30A, 10V  70-220AB  70-220AB	Series	STripFET?
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C60A (Tc)Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs70nC @ 5VInput Capacitance (Ciss) (Max) @ Vds4150pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs14 mOhm @ 30A, 10VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14 mOhm @ 30A, 10V  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  Package / Case  60A (Tc)  60	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs70nC @ 5VInput Capacitance (Ciss) (Max) @ Vds4150pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)150W (Tc)Rds On (Max) @ Id, Vgs14 mOhm @ 30A, 10VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  TonC @ 5V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14 mOhm @ 30A, 10V  Operating Temperature  175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  TO-220AB	Current - Continuous Drain (Id) @ 25°C	60A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  4150pF @ 25V  Vgs (Max)  ±15V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14 mOhm @ 30A, 10V  Operating Temperature  175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB  Package / Case  TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 4150pF @ 25V  Vgs (Max) ±15V  FET Feature	Vgs(th) (Max) @ Id	2.5V @ 250μA
Vgs (Max) ±15V  FET Feature -  Power Dissipation (Max) 150W (Tc)  Rds On (Max) @ Id, Vgs 14 mOhm @ 30A, 10V  Operating Temperature 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220AB  Package / Case TO-220-3	Gate Charge (Qg) (Max) @ Vgs	70nC @ 5V
FET Feature - T50W (Tc)  Rds On (Max) @ Id, Vgs 14 mOhm @ 30A, 10V  Operating Temperature 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220AB  Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	4150pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  14 mOhm @ 30A, 10V  Operating Temperature  175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB  Package / Case  TO-220-3	Vgs (Max)	±15V
Rds On (Max) @ Id, Vgs 14 mOhm @ 30A, 10V  Operating Temperature 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220AB  Package / Case TO-220-3	FET Feature	-
Operating Temperature 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220AB  Package / Case TO-220-3	Power Dissipation (Max)	150W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	14 mOhm @ 30A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
•	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

#### STP60NE06L-16 Guarantees



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## STP60NE06L-16 Payment Methods



















## STP60NE06L-16 Shipping Methods













If you have any question about STP60NE06L-16, please do not hesitate to contact us!

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